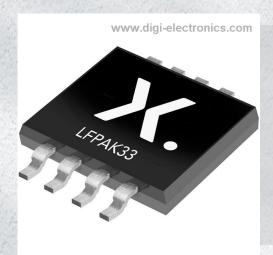


BUK9M156-100EX Datasheet



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DiGi Electronics Part Number BUK9M156-100EX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number BUK9M156-100EX

Description MOSFET N-CH 100V 9.3A LFPAK33

Detailed Description N-Channel 100 V 9.3A (Tc) 36W (Tc) Surface Mount

LFPAK33



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer:
Nexperia USA Inc.
Product Status:
Active
Technology:
MOSFET (Metal Oxide)
Current - Continuous Drain (Id) @ 25°C:
9.3A (Tc)
Rds On (Max) @ Id, Vgs:
150mOhm @ 5A, 10V
Gate Charge (Qg) (Max) @ Vgs:
7.4 nC @ 5 V
Input Capacitance (Ciss) (Max) @ Vds:
695 pF @ 25 V
Power Dissipation (Max):
36W (Tc)
Grade:
Automotive
Mounting Type:
Surface Mount
Package / Case:
SOT-1210, 8-LFPAK33 (5-Lead)

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



BUK9M156-100E

N-channel 100 V, 156 mΩ logic level MOSFET in LFPAK33

19 September 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	9.3	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	36	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	124	156	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	3.2	-	nC



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D I
2	S	Source		
3	S	Source		G_U: 4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9M156-100E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M156-100E	915610

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	100	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	36	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	9.3	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	6.5	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	37	Α

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Symbol	Parameter	Conditions		Min	Max	Unit	
T _{stg}	storage temperature			-55	175	°C	
Tj	junction temperature			-55	175	°C	
Source-drain	Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	9.3	Α	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	37	Α	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 9.3 A; $V_{sup} \le 100$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[3][4]	-	9.6	mJ	

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_j and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

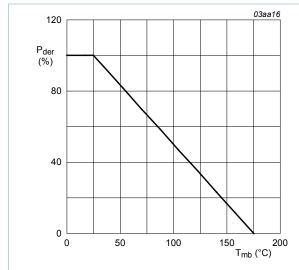


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

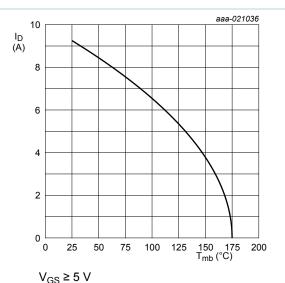
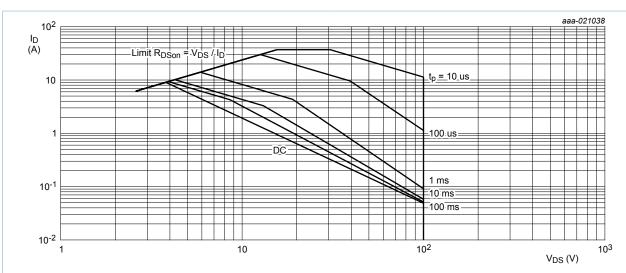


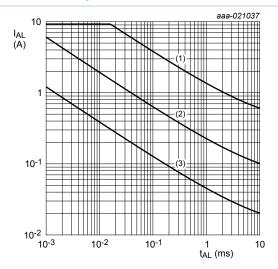
Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 9.3A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



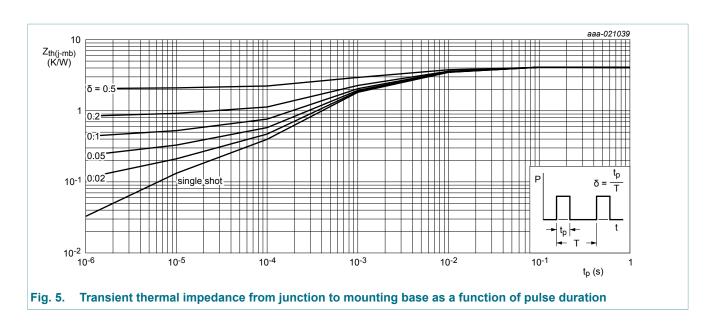
(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	3.61	4.17	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS} drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V	
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V	
	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 175 °C; Fig. 10	0.5	-	-	V	
I _{DSS} drain leakage current	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	124	156	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	120	150	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	420	mΩ
Dynamic cl	naracteristics		1			
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	7.4	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	1.4	-	nC
Q_{GD}	gate-drain charge		-	3.2	-	nC

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N-channel 100 V, 156 m Ω logic level MOSFET in LFPAK33

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	523	695	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	42	50	pF
C _{rss}	reverse transfer capacitance		-	28	39	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R_{L} = 10 Ω ; V_{GS} = 5 V;	-	5.6	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	8.8	-	ns
t _{d(off)}	turn-off delay time		-	11.8	-	ns
t _f	fall time		-	7.2	-	ns
Source-dra	ain diode			'		,
V _{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-	0.92	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	27.6	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	33.9	-	nC

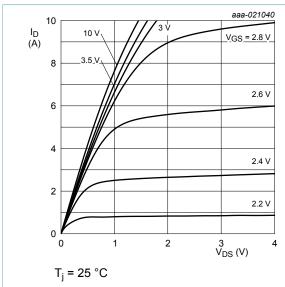


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

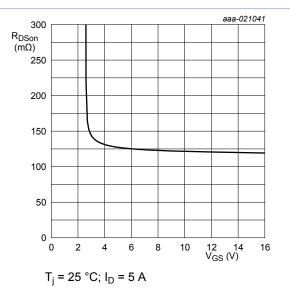


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

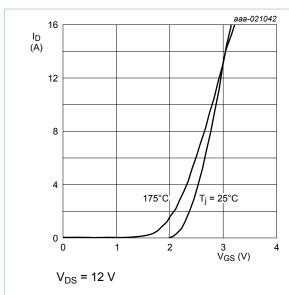


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

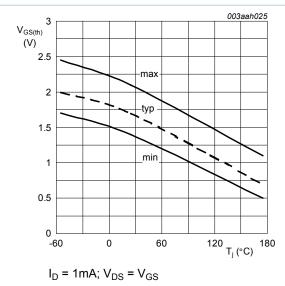


Fig. 10. Gate-source threshold voltage as a function of junction temperature

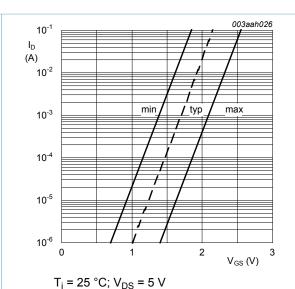


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

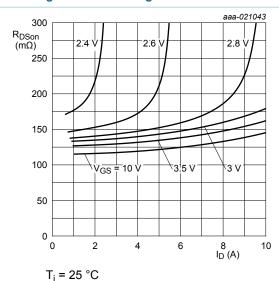


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

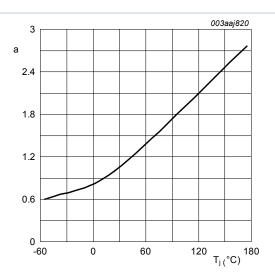


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

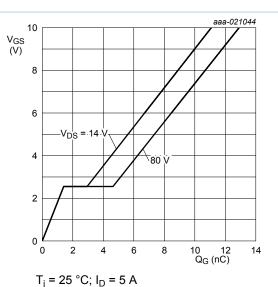


Fig. 13. Gate-source voltage as a function of gate charge; typical values

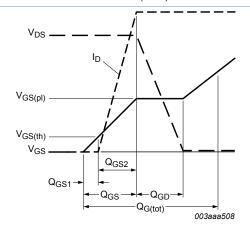
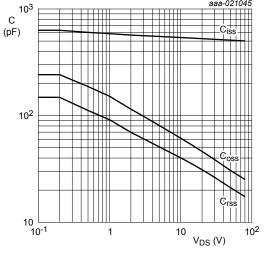
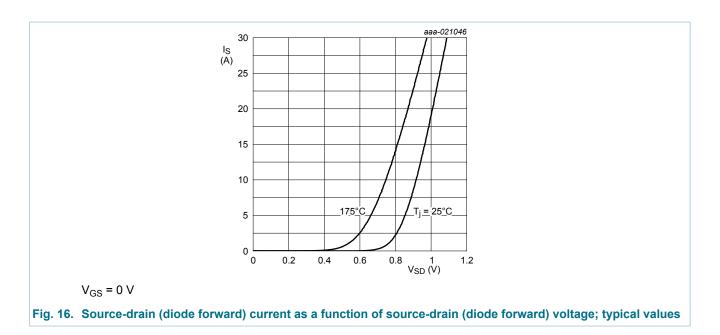


Fig. 14. Gate charge waveform definitions



 $V_{GS} = 0 V; f = 1 MHz$

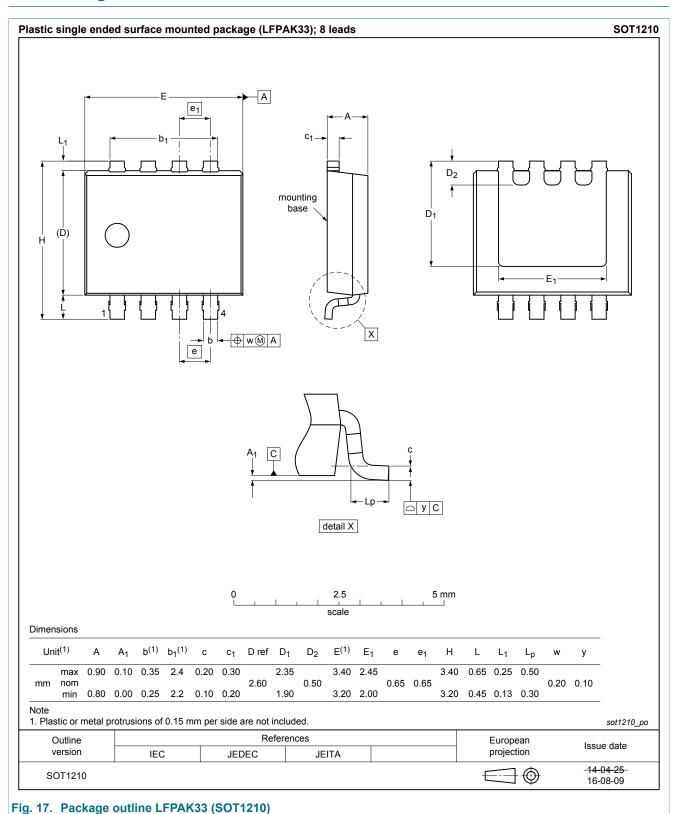
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

12. Package outline



13. Legal information

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N-channel 100 V, 156 mΩ logic level MOSFET in LFPAK33

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